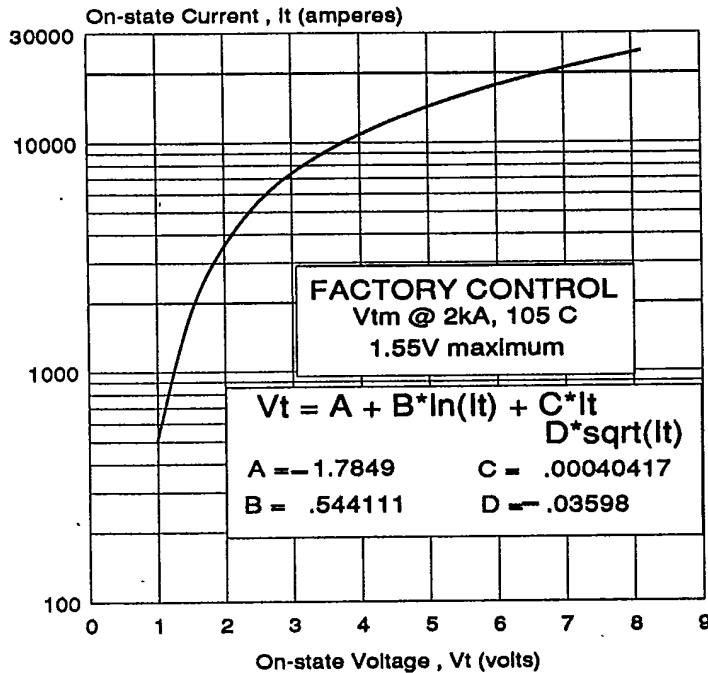


GE CO/ STATIC PWR CMPNT 53E D 3874584 0000135 739 GES P

The X6RD207 thyristor features the proven 77mm diameter silicon junction design manufactured by the GE mult-diffusion process. It is housed in an experimental thin disc-type package for use where space constraints are severe. Additional features are lighter weight and lower thermal resistance compared to the conventional GE PressPak.

ON-STATE CHARACTERISTIC
Process Maximum @ $T_J=105^\circ\text{C}$

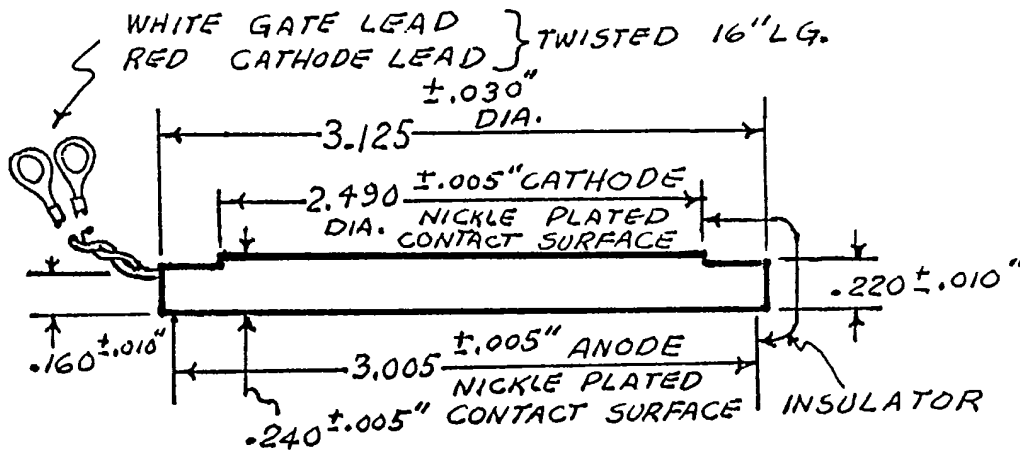


PRINCIPAL RATINGS AND CHARACTERISTICS

Repetitive peak off-state & reverse volts	V_{DRM} V_{RRM}	$T_J=0$ to 125°C	up to 4500	V
Repetitive working crest voltage	V_{DWM} V_{DRM}	$T_J=0$ to 125°C	$0.8V_{DRM}$ $0.8V_{RRM}$	
Off-state & reverse leakage current	I_{DWM} I_{RRM}	$T_J=0$ to 125°C	100 100	ma
Average on-state current	$I_{T(AV)}$	$T_{JRM}=70^\circ\text{C}$	1500	A
Peak half-cycle non-rep surge current	I_{TSM}	60 Hz 50 Hz	26 24	kA
On-state voltage	V_{TM}	$I_T=2000A$ $t_T=8.3ms$ $T_J=125^\circ\text{C}$	1.55	V
Critical rate of rise of on-state current	di/dt rep	$T_J=125^\circ\text{C}$ 60 Hz	100	A/us
Critical rate of rise of off-state voltage	dv/dt	$T_J=125^\circ\text{C}$ $V_D=.67V_{DRM}$	1000	V/us
Recovery current	I_{RM}	$T_J=125^\circ\text{C}$ 2A/us 5A/us	85 180	A
Turn-off time	T_{off}	5A/us, -100V 20V/us to 2000V	500	us
Thermal resistance	$R_{\theta JC}$		.007	c/w
Externally applied	F		8000-	lbs.

90e:thinpak3/12/91

MECHANICAL OUTLINE



GE - STATIC POWER COMPONENT OPERATION
205 Great Valley Parkway, Malvern PA 19355 USA

V913 3/12/91